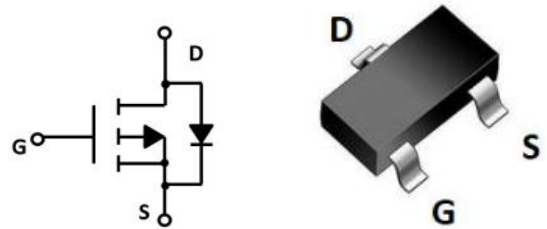


**SOT-23 -30V P Channel Enhancement 沟道增强型
MOS Field Effect Transistor 场效应管**



■ Absolute Maximum Ratings 最大额定值

| Characteristic 特性参数 | Symbol 符号 | Rat 额定值 | Unit 单位 |
|--|--------------------------------|----------|--------------|
| Drain-Source Voltage 漏极-源极电压 | BV_{DSS} | -30 | V |
| Gate- Source Voltage 栅极-源极电压 | V_{GS} | ± 20 | V |
| Drain Current (continuous)漏极电流-连续 | I_D (at $T_A = 25^\circ C$) | -3 | A |
| Drain Current (pulsed)漏极电流-脉冲 | I_{DM} | -20 | A |
| Total Device Dissipation 总耗散功率 | P_D (at $T_A = 25^\circ C$) | 1100 | mW |
| Thermal Resistance Junction-Ambient 热阻 | $R_{\theta JA}$ | 113 | $^\circ C/W$ |
| Junction/Storage Temperature 结温/储存温度 | T_J, T_{stg} | -55~150 | $^\circ C$ |

■ Device Marking 产品字标

FS2307AM=S7A

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

| Characteristic 特性参数 | Symbol 符号 | Min 最小值 | Typ 典型值 | Max 最大值 | Unit 单位 |
|--|--------------|------------|------------|------------|------------------|
| Drain-Source Breakdown Voltage 漏极-源极击穿电压($I_D = -250\mu\text{A}, V_{GS}=0\text{V}$) | BV_{DSS} | -30 | — | — | V |
| Gate Threshold Voltage 栅极开启电压($I_D = -250\mu\text{A}, V_{GS}=V_{DS}$) | $V_{GS(th)}$ | -1 | -1.5 | -2.2 | V |
| Zero Gate Voltage Drain Current 零栅压漏极电流($V_{GS}=0\text{V}, V_{DS}= -30\text{V}$) | I_{DSS} | — | — | 1 | μA |
| Gate Body Leakage 栅极漏电流($V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$) | I_{GSS} | — | — | ± 100 | nA |
| Static Drain-Source On-State Resistance 静态漏源导通电阻($I_D= -3\text{A}, V_{GS}= -10\text{V}$) ($I_D= -2\text{A}, V_{GS}= -4.5\text{V}$) | $R_{DS(ON)}$ | — | 64 95 | 75 109 | $\text{m}\Omega$ |
| Diode Forward Voltage Drop 内附二极管正向压降($I_{SD}= -3\text{A}, V_{GS}=0\text{V}$) | V_{SD} | — | — | -1.2 | V |
| Input Capacitance 输入电容 ($V_{GS}=0\text{V}, V_{DS}= -10\text{V}, f=1\text{MHz}$) | C_{ISS} | — | 365 | — | pF |
| Common Source Output Capacitance 共源输出电容($V_{GS}=0\text{V}, V_{DS}= -10\text{V}, f=1\text{MHz}$) | C_{OSS} | — | 59 | — | pF |
| Reverse Transfer Capacitance 反馈电容($V_{GS}=0\text{V}, V_{DS}= -10\text{V}, f=1\text{MHz}$) | C_{RSS} | — | 45 | — | pF |
| Total Gate Charge 栅极电荷密度 ($V_{DS}= -15\text{V}, I_D= -3\text{A}, V_{GS}= -10\text{V}$) | Q_g | — | 8 | — | nC |
| Gate Source Charge 栅源电荷密度 ($V_{DS}= -15\text{V}, I_D= -3\text{A}, V_{GS}= -10\text{V}$) | Q_{gs} | — | 2 | — | nC |
| Gate Drain Charge 栅漏电荷密度 ($V_{DS}= -15\text{V}, I_D= -3\text{A}, V_{GS}= -10\text{V}$) | Q_{gd} | — | 1 | — | nC |
| Turn-ON Delay Time 开启延迟时间 ($V_{DS}= -15\text{V}, I_D= -1\text{A}, R_{GEN}=2.5\Omega, V_{GS}= -10\text{V}$) | $t_{d(on)}$ | — | 3 | — | ns |
| Turn-ON Rise Time 开启上升时间 ($V_{DS}= -15\text{V}, I_D= -1\text{A}, R_{GEN}=2.5\Omega, V_{GS}= -10\text{V}$) | t_r | — | 18 | — | ns |
| Turn-OFF Delay Time 关断延迟时间 ($V_{DS}= -15\text{V}, I_D= -1\text{A}, R_{GEN}=2.5\Omega, V_{GS}= -10\text{V}$) | $t_{d(off)}$ | — | 18 | — | ns |
| Turn-OFF Fall Time 关断下降时间 ($V_{DS}= -15\text{V}, I_D= -1\text{A}, R_{GEN}=2.5\Omega, V_{GS}= -10\text{V}$) | t_f | — | 23 | — | ns |

■ Typical Characteristic Curve 典型特性曲线

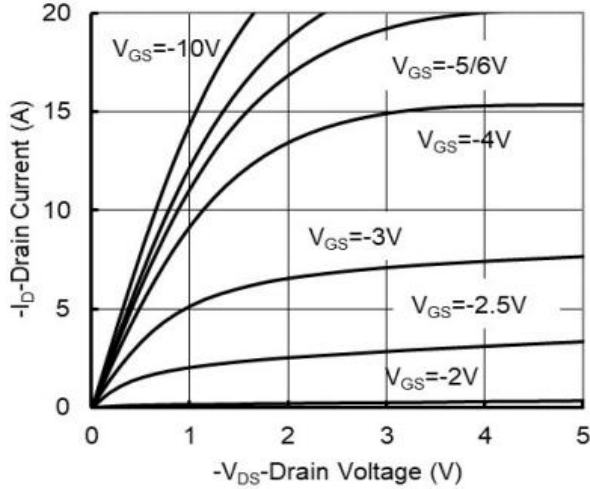


Figure 1: Output Characteristics

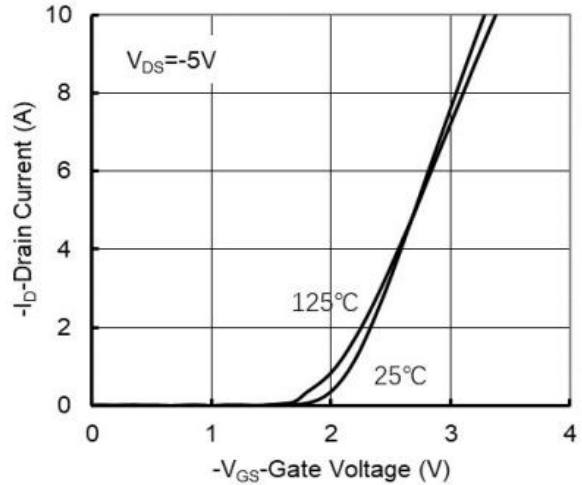


Figure 2: Transfer Characteristics

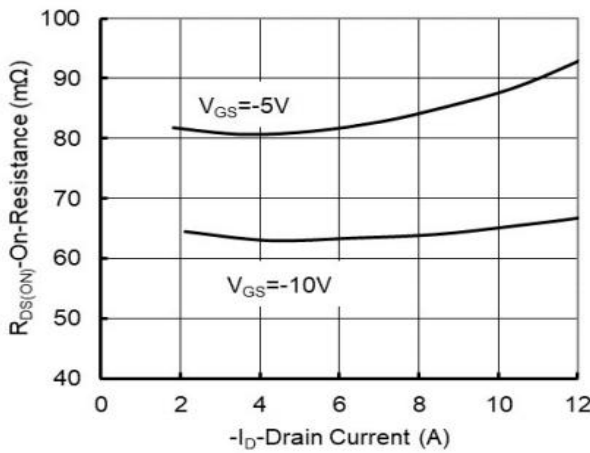


Figure 3: On-Resistance vs. Drain Current

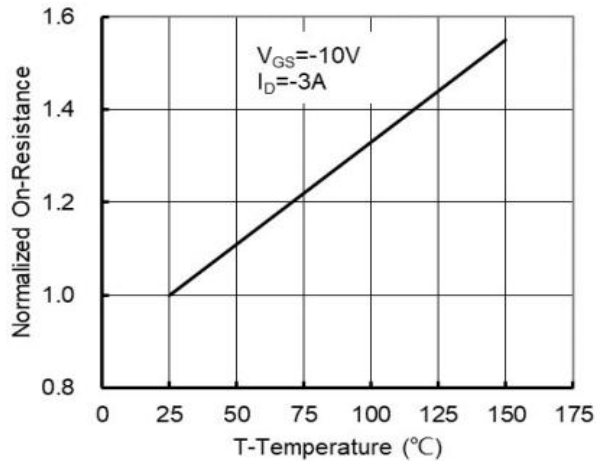


Figure 4: On-Resistance vs. Temperature

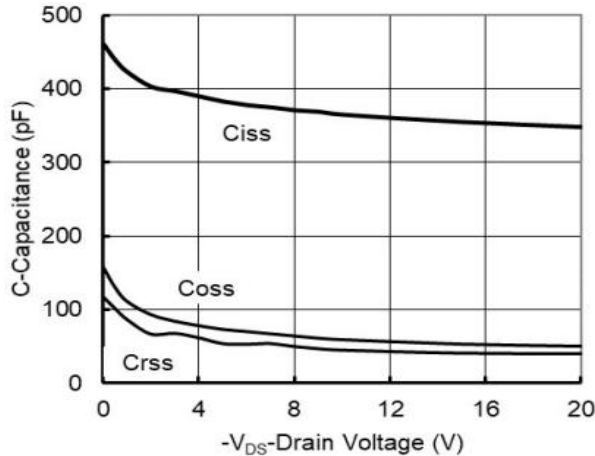


Figure 5: Capacitance Characteristics

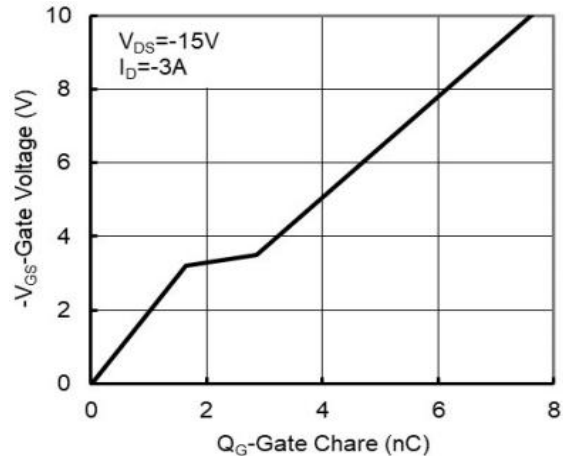


Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

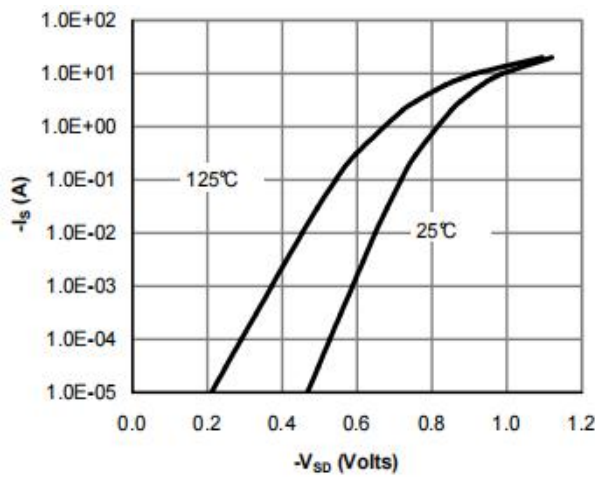


Figure 7: Diode Characteristics

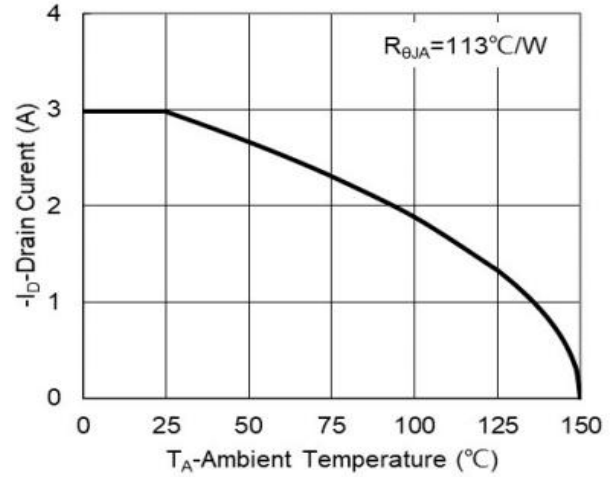


Figure 8: Drain Current vs. Temperature

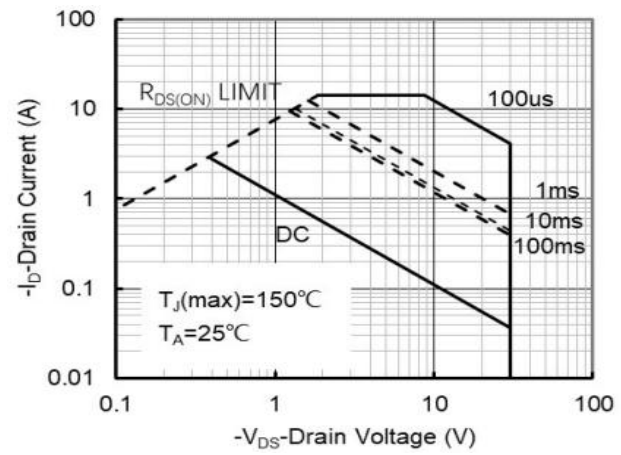


Figure 9: Safe Operating Area

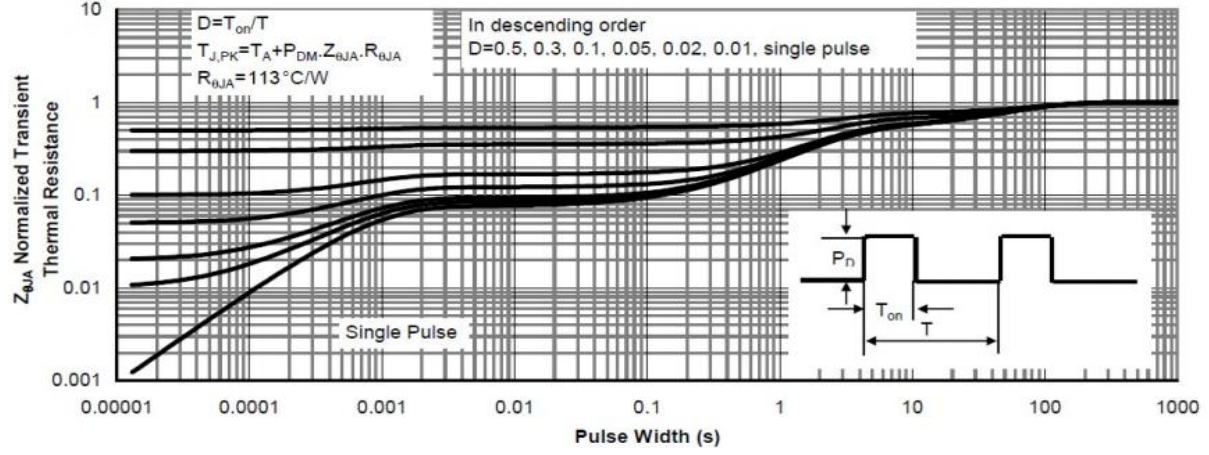
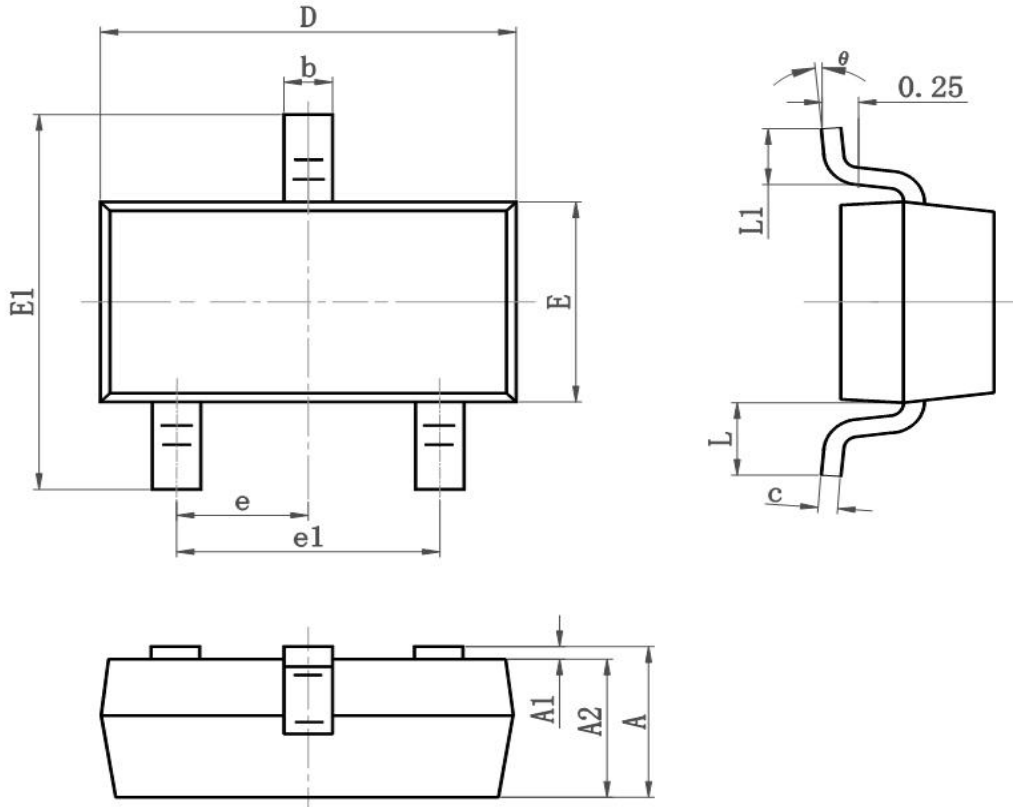


Figure 10: Transient Thermal Response Curve

■ Dimension 外形封装尺寸



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.050 | 0.055 |
| EI | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.900 | 1.00 | 0.035 | 0.039 |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.500 | 0.600 | 0.020 | 0.024 |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |